6MBI75UC-120

IGBT Module U-Series 1200V / 75A 6 in one-package

■ Features

· High speed switching
· Voltage drive
· Low inductance module structure

■ Applications

· Inverter for Motor drive
· AC and DC Servo drive amplifier
· Uninterruptible power supply
· Industrial machines, such as Welding machines

■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item	Symbol	Conditions		Rating	Unit
Collector-Emitter voltage	V_{CES}			1200	V
Gate-Emitter voltaga	V_{GES}			±20	V
Collector current	I_C	Continuous	Tc=25°C	100	A
			Tc=80°C	75	
	I_{CP}	1ms	Tc=25°C	200	
			Tc=80°C	150	
	-I_C			75	
	-I_C pulse			150	
Collector Power Dissipation	P_C	1 device		390	W
Junction temperature	T_j			+150	℃
Storage temperature	T_{stg}			-40 to +125	
Isolation voltage between terminal and copper base *1	V_{iso}	AC:1min.		2500	VAC
Screw Torque Mounting *2				3.5	N·m

*1 : All terminals should be connected together when isolation test will be done.
*2 : Recommendable value : 2.5 to 3.5 N·m(M5)

● Electrical characteristics (at Tj=25°C unless otherwise specified)

Item	Symbols	Conditions		Characteristics Min.	Typ.	Max.	Unit
Zero gate voltage collector current	I_{CES}	V_{GE}=0V, V_{CE}=1200V		–	–	1.0	mA
Gate-Emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=±20V		–	–	200	nA
Gate-Emitter threshold voltage	$V_{GE(th)}$	V_{CE}=20V, I_C=75mA		4.5	6.5	8.5	V
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (chip)	V_{GE}=15V, I_C=75A	Tj=25°C	–	1.75	2.10	V
			Tj=125°C	–	2.00	–	
Input capacitance	C_{ies}	V_{CE}=10V, V_{GE}=0V, f=1MHz		–	8	–	nF
Turn-on time	t_{on}	V_{CC}=600V		–	0.36	1.20	µs
	t_r	I_C=75A		–	0.21	0.60	
	$t_{r(i)}$	V_{GE}=±15V		–	0.03	–	
Turn-off time	t_{off}	R_G=9.1 Ω		–	0.37	1.00	
	t_f			–	0.07	0.30	
Forward on voltage	V_F	V_{GE}=0V	Tj=25°C	–	1.60	1.90	V
	(chip)	I_F=75A	Tj=125°C	–	1.70	–	
Reverse recovery time	t_{rr}	I_F=75A		–	–	0.35	µs
Lead resistance, terminal-chip*3	R lead	Without shunt resistance		–	5.7	–	mΩ
Shunt resistance	R shunt	Resistance of R1,R2,R3 *4		–	2.4	–	

*3: Biggest internal terminal resistance among arm.
*4: R1, R2,R3 is shown in equivalent circuit (p5)

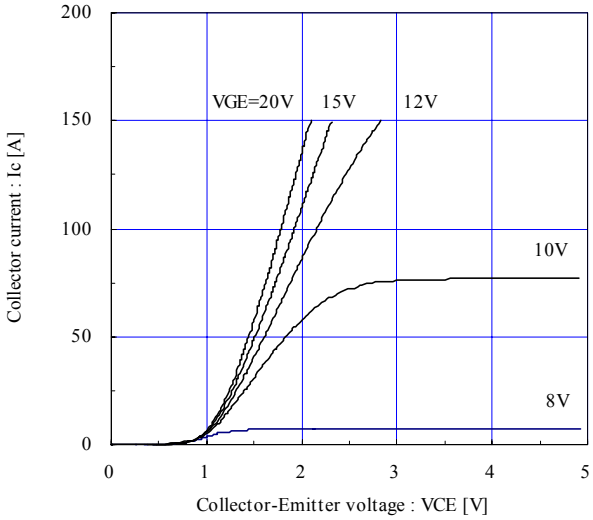
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics Min.	Typ.	Max.	Unit
Thermal resistance	Rth(j-c)	IGBT	–	–	0.32	°C/W
	Rth(j-c)	FWD	–	–	0.49	°C/W
Contact Thermal resistance	Rth(c-f)*5	With thermal compound	–	0.05	–	°C/W

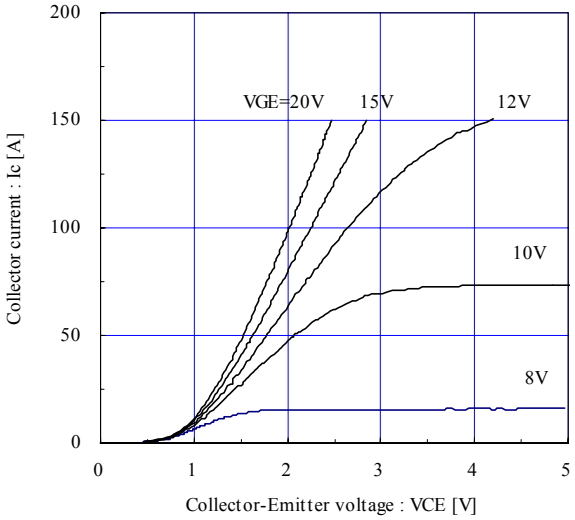
*5 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

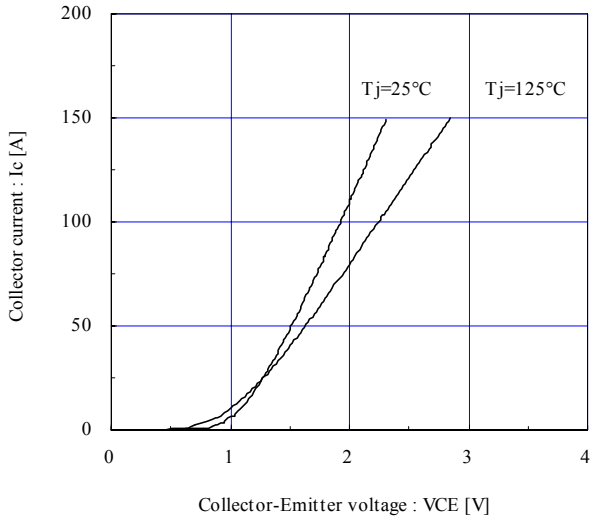
Collector current vs. Collector-Emitter voltage (typ.)
Tj= 25°C / chip



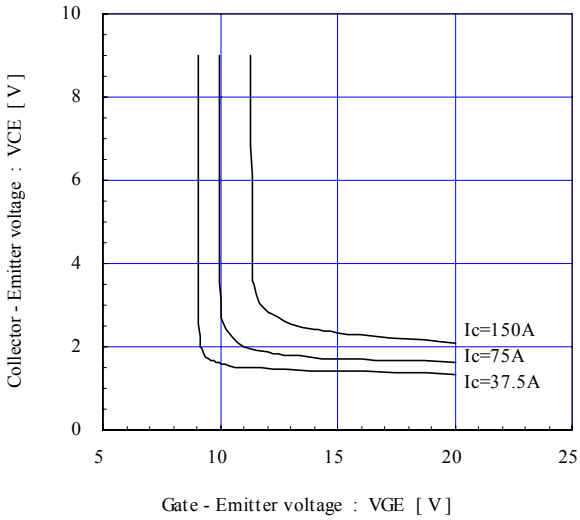
Collector current vs. Collector-Emitter voltage (typ.)
Tj= 125°C / chip



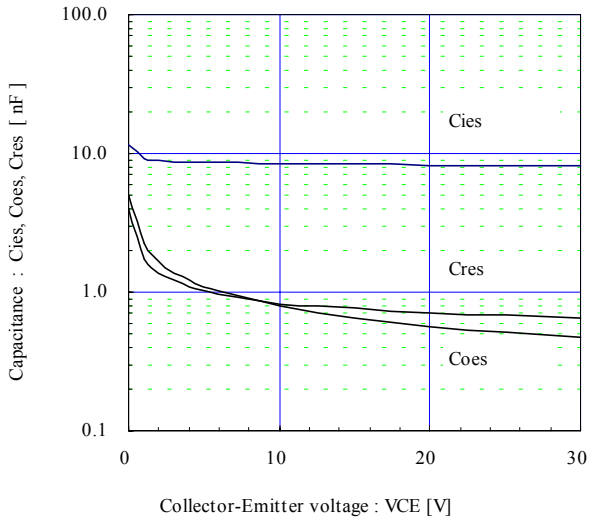
Collector current vs. Collector-Emitter voltage (typ.)
VGE=15V / chip



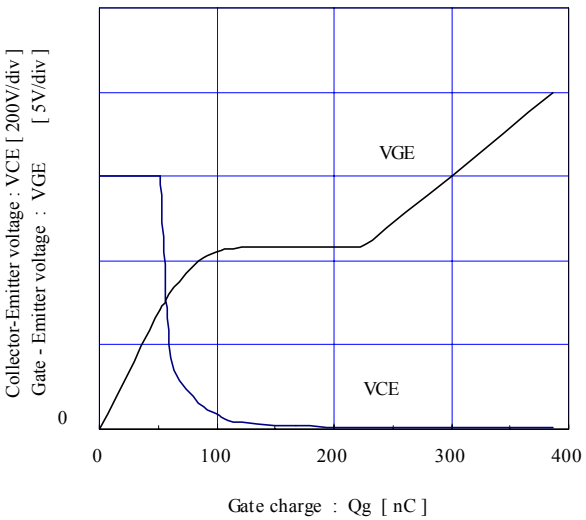
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
Tj=25°C / chip



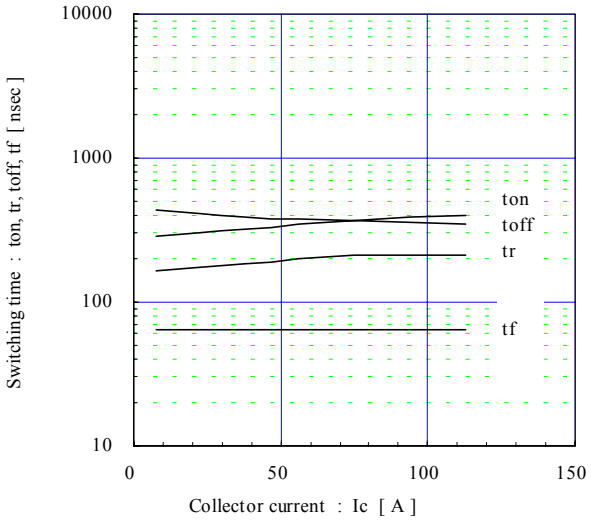
Capacitance vs. Collector-Emitter voltage (typ.)
VGE=0V, f= 1MHz, Tj= 25°C



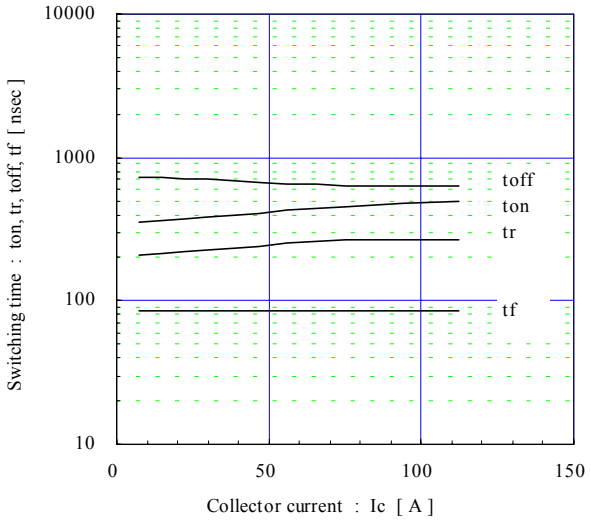
Dynamic Gate charge (typ.)
Vcc=600V, Ic=75A, Tj= 25°C



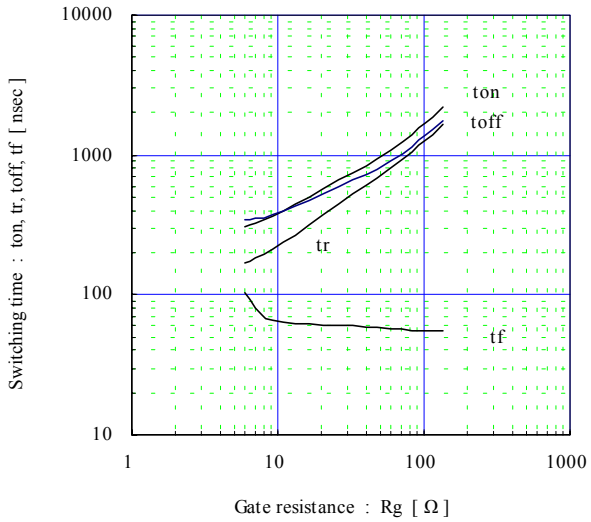
Switching time vs. Collector current (typ.)
Vcc=600V, VGE=±15V, Rg=9.1Ω, Tj= 25°C



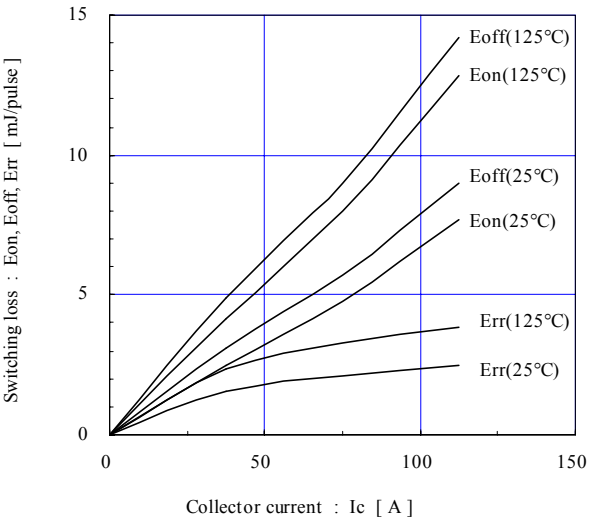
Switching time vs. Collector current (typ.)
Vcc=600V, VGE=±15V, Rg=9.1Ω, Tj=125°C



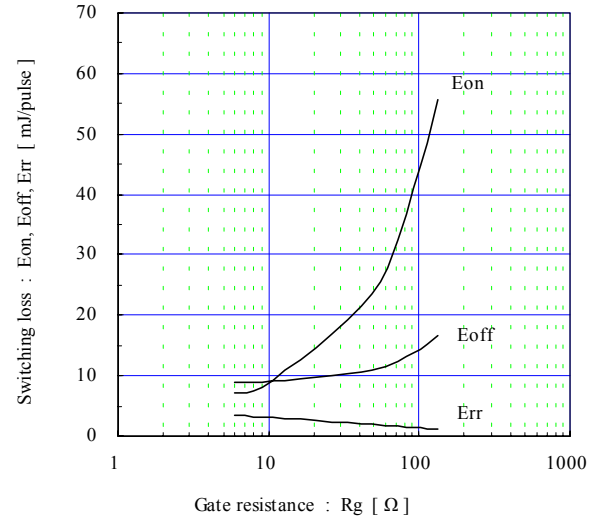
Switching time vs. Gate resistance (typ.)
Vcc=600V, Ic=75A, VGE=±15V, Tj= 25°C



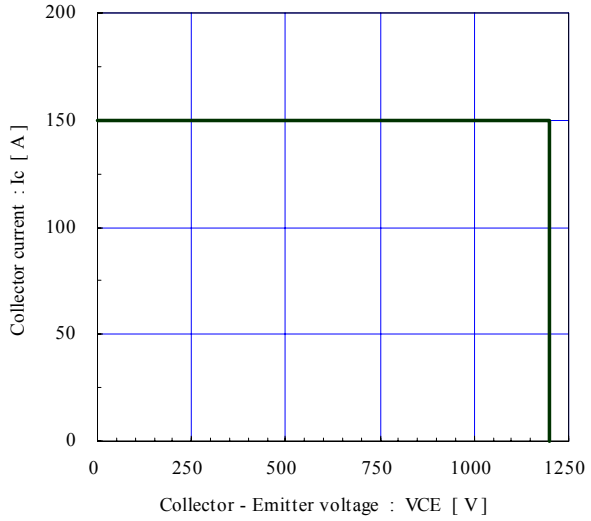
Switching loss vs. Collector current (typ.)
Vcc=600V, VGE=±15V, Rg=9.1Ω



Switching loss vs. Gate resistance (typ.)
Vcc=600V, Ic=75A, VGE=±15V, Tj= 125°C

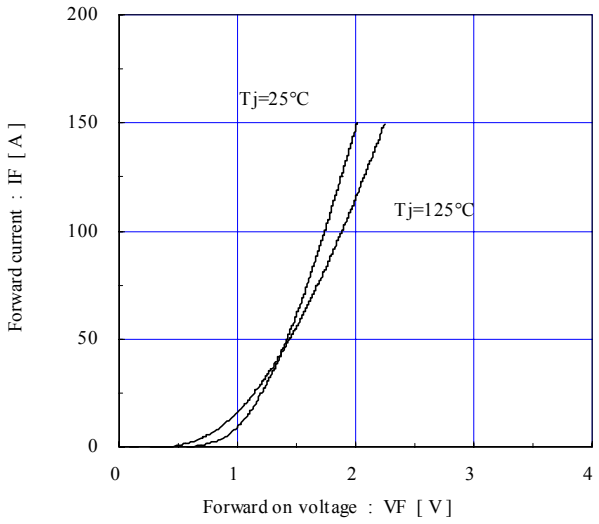


Reverse bias safe operating area (max.)
+VGE=15V,-VGE <= 15V, RG >= 9.1Ω ,Tj <= 125°C



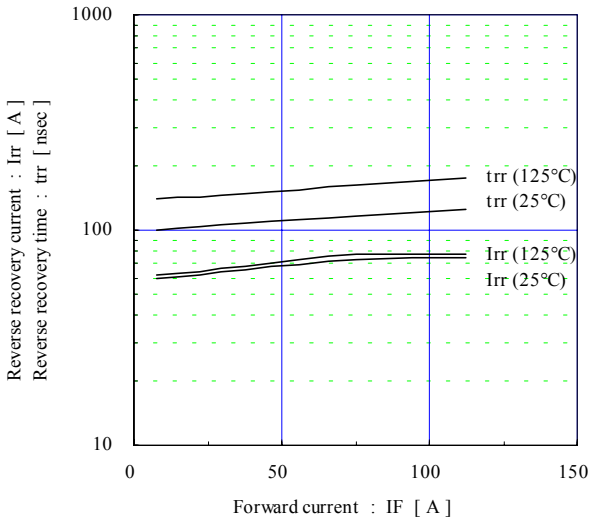
Forward current vs. Forward on voltage (typ.)

chip

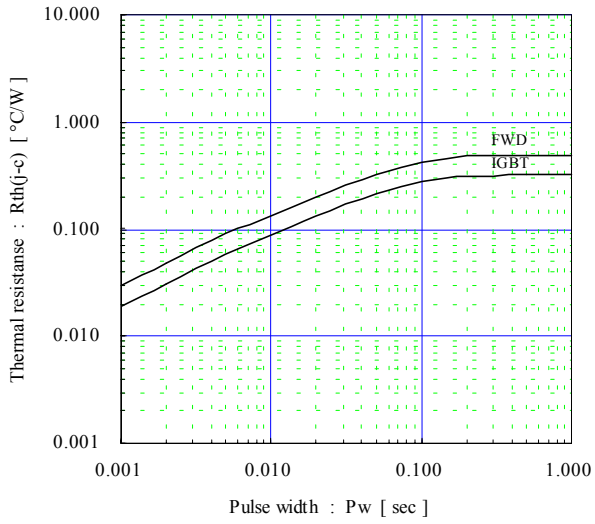


Reverse recovery characteristics (typ.)

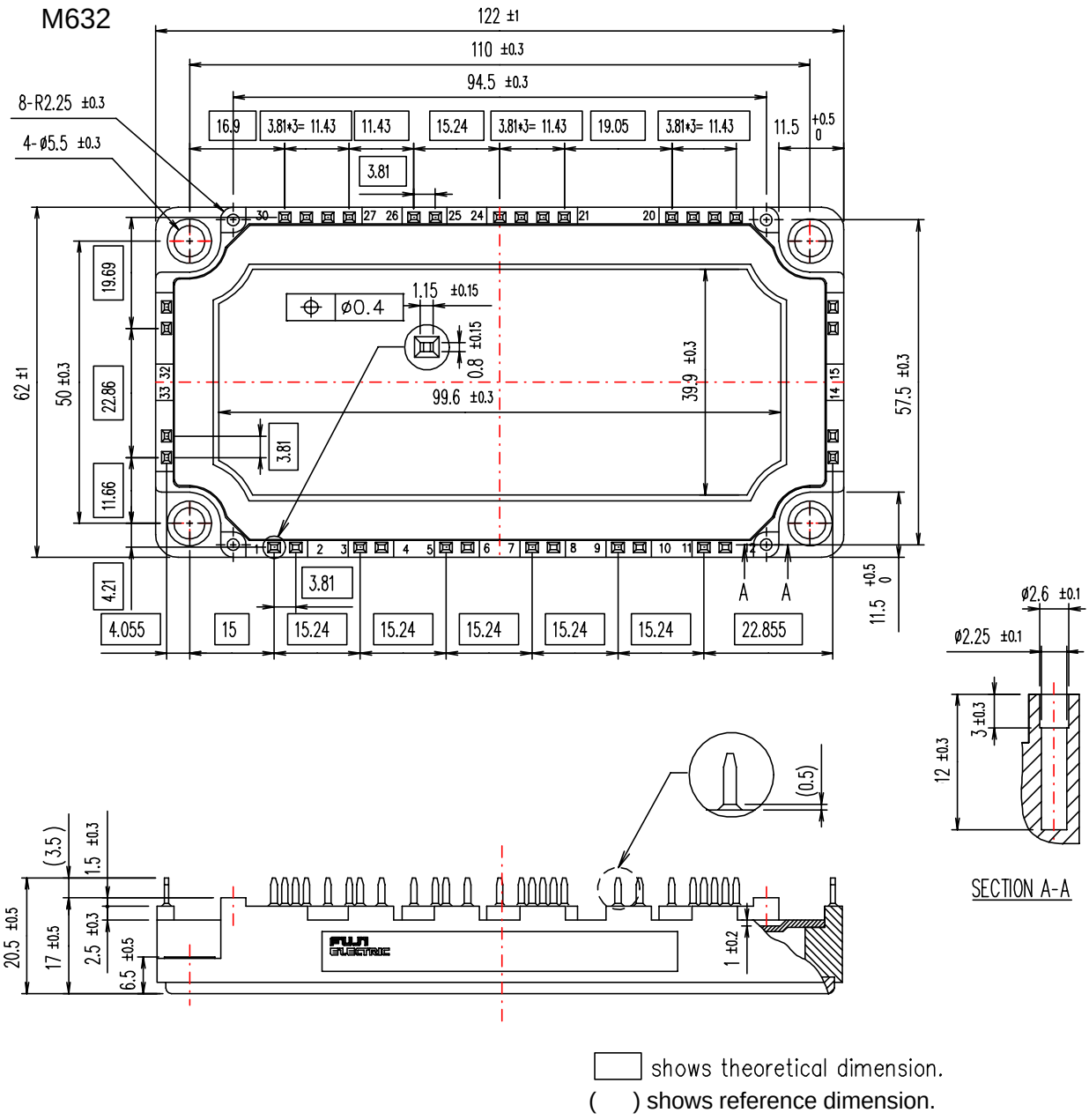
Vcc=600V, VGE=±15V, Rg=9.1Ω



Transient thermal resistance (max.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic